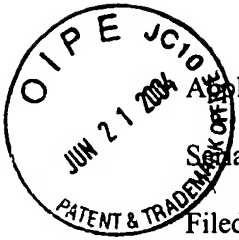


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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Yu Min Lin, et al.	§	Docket No.:	2002-1057 / 24061.69
Serial No.:	10/763,643	§	Art Unit:	2812
Filed:	January 23, 2004	§	Examiner:	To Be Determined
Entitled:	System and Method for Integration of HfO2 and RTCVD Ply-Silicon	§ § § § § §		

INFORMATION DISCLOSURE STATEMENT

Mail Stop: Amendment  
Commissioner For Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

In compliance with the duty of disclosure under 37 CFR §1.56, and in accordance with the practice under 37 CFR §1.97 and §1.98, the Examiner's attention is directed to the documents listed on the enclosed modified Form PTO-1449. No inference should be made that the cited references are in fact material, are in fact prior art, or that no better art exists. The cited patents are listed in numerical order and are not in any order based on their pertinence.

The above-identified application was filed after June 30, 2003. Therefore, pursuant to the waiver of the requirement under 37 CFR 1.98 (a)(2)(i) as stated in a Pre-OG Notice dated July 11, 2003, copies of the U.S. patents listed on the enclosed modified Form PTO-1449 are not being provided.

This Information Disclosure Statement is being filed within three months of the United States filing date or before the mailing date of a first Office Action on the merits. No certification or fee is required (37 CFR §1.97(b)).

It is respectfully requested that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be returned indicating that such information has been considered.

Respectfully submitted,

David M. O'Dell  
Registration No. 42,044

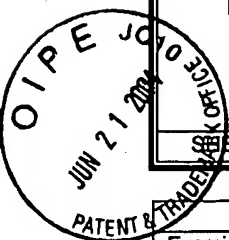
Date: 6-16-04

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Date



In place of PTO-1449 Form	U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		Complete if Known		
			Application Number	10/763,643	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)			Filing Date	January 23, 2004	
			Applicant(s)	Yu Min Lin, et al.	
			Art Unit	2812	
			Examiner Name	TBD	
SHEET	1	OF	1	Attorney Docket Number	2002-1057 / 24061.69

U. S. PATENT DOCUMENTS				
Examiner's Initials	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
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FOREIGN PATENT DOCUMENTS					
Examiner's Initials	Cite No.	Foreign Patent Document (Country Code - Number - Kind)	Publication Date MM-DD-YYYY	Patentee or Applicant of Cited Document	Translation Y/N

OTHER PRIOR ART		
Examiner's Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item, date, page(s), volume-issue number(s), publisher, city/country where published
	AP	WORLD WIDE WEB, <a href="http://www.mrs.org/publications/jmr/jmra/2003/jan/009.html">www.mrs.org/publications/jmr/jmra/2003/jan/009.html</a> , Choi, Kyu-Jeong, et al., "Ultrathin HfO <sub>2</sub> Gate Dielectric Grown by Plasma-Enhanced Chemical Vapor Deposition Using Hf [OC(CH <sub>3</sub> ) <sub>3</sub> ] <sub>4</sub> as a Precursor in the Absence of O <sub>2</sub> ", printed on March 4, 2003, 1 page.
	AQ	KING, Susan J., "Characterising the Interface Trap Density of Si:P Quantum Computer Devices", School of Electrical Engineering & Telecommunications, 2002, 1 page.
	AR	LIN, Y.S., et al, "Dielectric Property and Thermal Stability of HfO <sub>2</sub> on Silicon", Applied Physics Letters, Volume 81, Number 11, September 9, 2002, pages 2041-2043.
	AS	Rashkeev, S.N., et al, "Physical Model for Enhanced Interface-Trap Formation at Low Dose Rates", Basic Mechanisms, Oral Presentation, Example Summary, 5 pages.

Examiner Signature		Date Considered	
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.